

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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WeEn Semiconductors





## 1. General description

Planar passivated high commutation three quadrant triac in a SOT78D (TO-220AB) internally insulated plastic package. This "series ET" triac triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers. It is used in applications where "high junction operating temperature" capability is required.

### 2. Features and benefits

- 3Q technology for improved noise immunity
- · Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High T<sub>j(max)</sub>
- Isolated mounting base with 2500 V (RMS) isolation
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

## 3. Applications

- Electronic thermostats (heating and cooling)
- Motor controls
- Refrigeration and air-conditioner compressor controls

## 4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ Fig. 4}; \text{ Fig. 5}$	-	-	100	A
Tj	junction temperature		-	-	150	°C
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 120 °C; <u>Fig. 1</u> ; <u>Fig. 2; Fig. 3</u>	-	-	10	A





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.5	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.5	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.5	-	10	mA
Dynamic ch	haracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; T <sub>j</sub> = 150 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	50	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 150 °C; $I_{T(RMS)}$ = 10 A; dV <sub>com</sub> /dt = 1 V/µs; gate open circuit	5	-	-	A/ms

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2		sym051
3	G	gate		5,
mb	n.c.	mounting base; isolated		
			() (	

# 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
BTA410Y-600ET	TO-220AB	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220	SOT78D

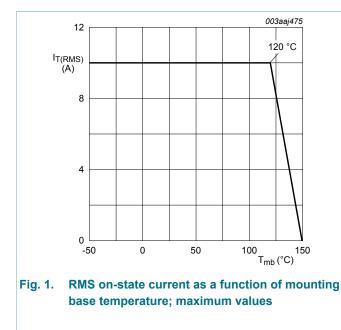
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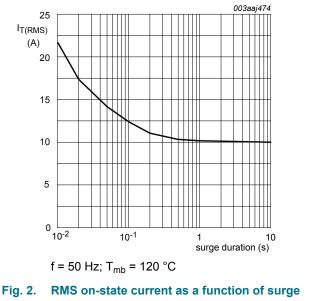
## 7. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

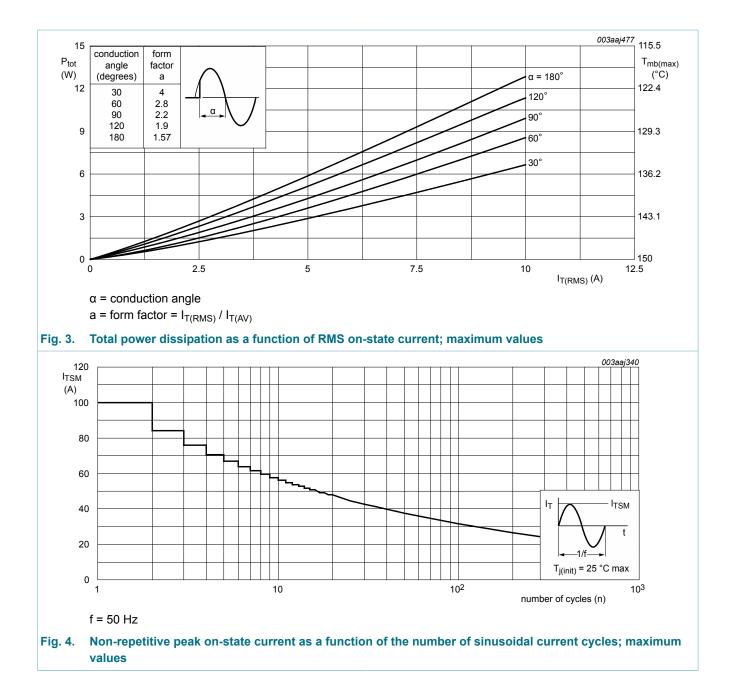
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 120 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	10	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ Fig. 4}; \text{ Fig. 5}$	-	100	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 16.7 \text{ ms}$	-	110	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	50	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 20 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/µs	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C





duration; maximum values

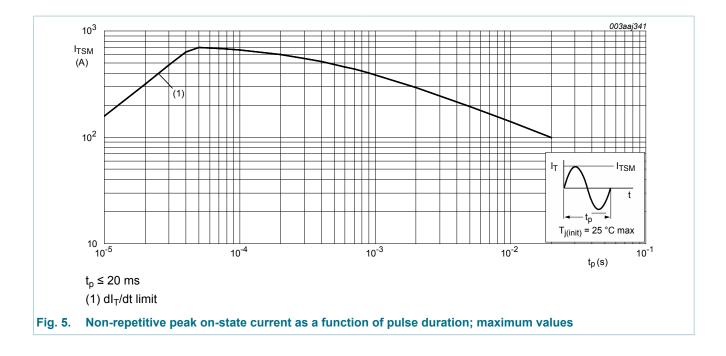
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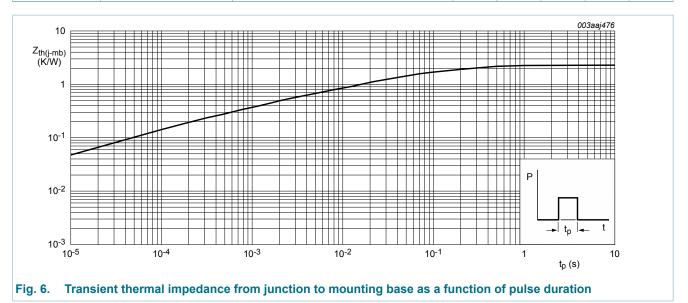
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## 8. Thermal characteristics

Table 5. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; <u>Fig. 6</u>	-	-	2.3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



## 9. Isolation characteristics

Table 6. Is	olation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>mb</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>mb</sub> = 25 °C	-	10	-	pF

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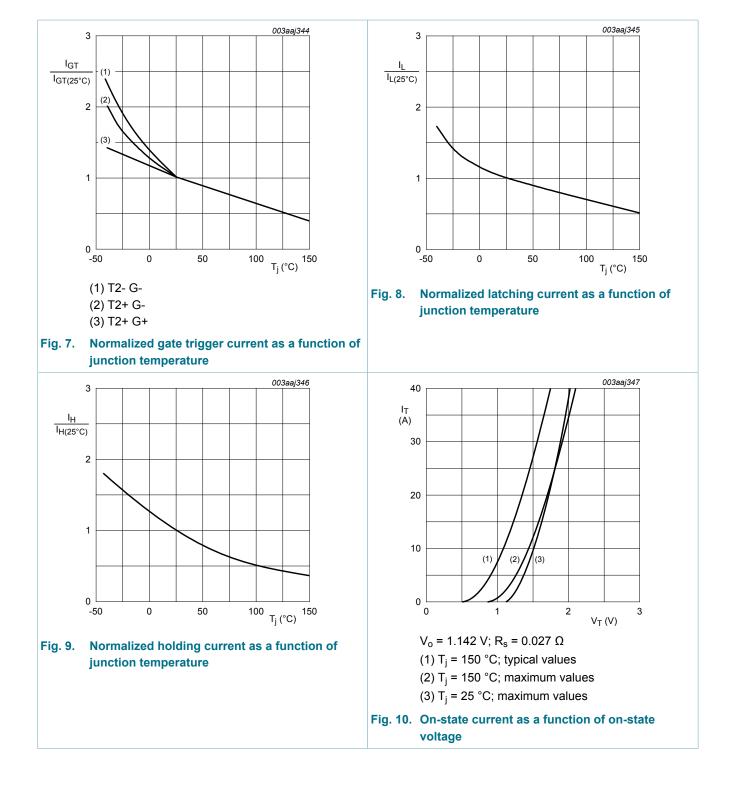
## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics	· · ·	1			-
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; Fig. 7	0.5	-	10	mA
		$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; Fig. 7	0.5	-	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	0.5	-	10	mA
l	latching current	$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G+};$ T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	25	mA
		$V_D$ = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	30	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-};$ T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	25	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	0.7	1	V
		V <sub>D</sub> = 400 V; T <sub>j</sub> = 150 °C; <u>Fig. 11</u>	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 150 °C	-	0.4	2	mA
Dynamic cl	naracteristics	· · ·	I			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; T <sub>j</sub> = 150 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	50	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_{D} = 400 \text{ V};  \text{T}_{\text{j}} = 150 \text{ °C};  \text{I}_{\text{T}(\text{RMS})} = 10 \text{ A};$ $dV_{\text{com}}/dt = 20 \text{ V}/\mu\text{s}; \text{ (snubberless condition); gate open circuit}$	2	-	-	A/ms
		$V_D = 400 \text{ V};  T_j = 150 \text{ °C};  I_{T(RMS)} = 10 \text{ A};$ $dV_{com}/dt = 10 \text{ V}/\mu\text{s}; \text{ gate open circuit}$	3.5	-	-	A/ms
		$V_D$ = 400 V; T <sub>j</sub> = 150 °C; I <sub>T(RMS)</sub> = 10 A; dV <sub>com</sub> /dt = 1 V/µs; gate open circuit	5	-	-	A/ms

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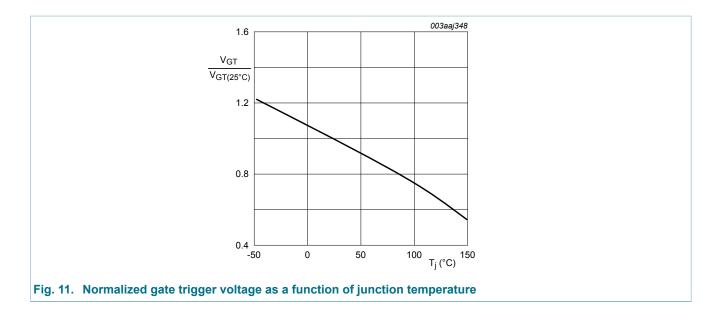
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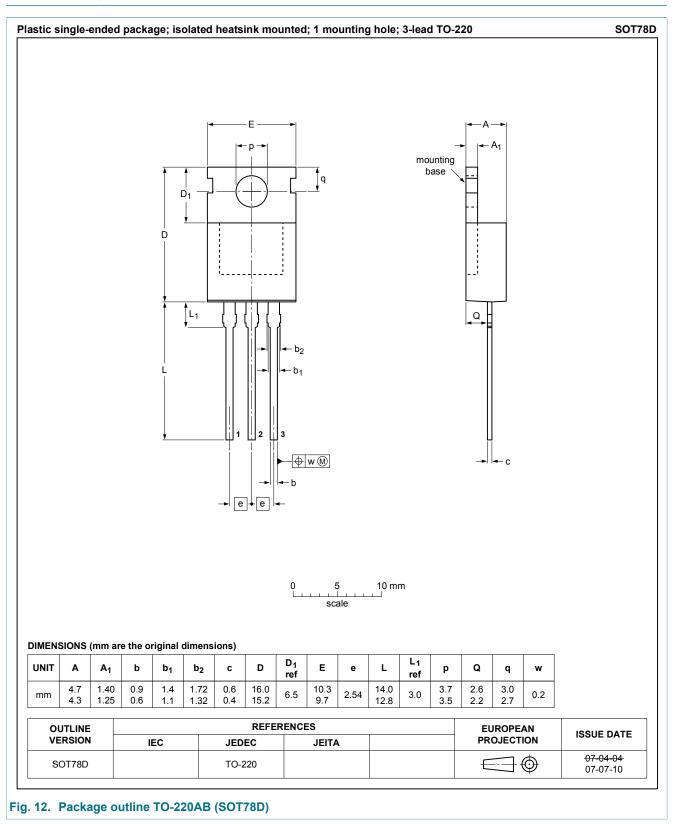
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## 11. Package outline



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#### **3Q Hi-Com Triac**

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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